





NPN SURFACE MOUNT TRANSISTOR

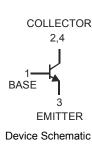
Features

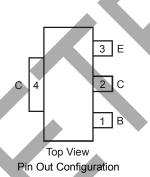
- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.055 grams (approximate)







Maximum Ratings @TA = 25°C unless otherwise specified

	Characteristic	Symbol	Value	Unit
Collector-Base Voltage		V _{CBO}	30	V
Collector-Emitter Voltage		V _{CEO}	25	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current		l _C	2.0	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

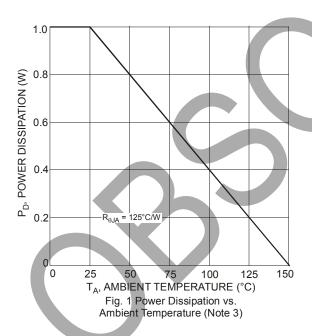
 Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

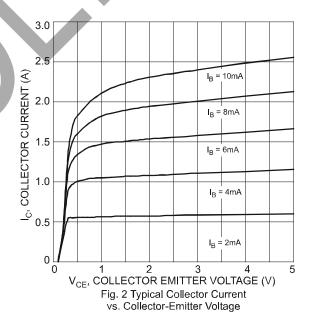


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	30	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	25	_	_	V	$I_C = 1mA, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	_		V	$I_C = 10\mu A, I_C = 0$
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 20V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)	ON CHARACTERISTICS (Note 4)					
DC Current Gain	h	200	_	400		$V_{CE} = 2.0V, I_{C} = 0.1A$
De current dann	h _{FE}	65	_			$V_{CE} = 2.0V, I_{C} = 1.5A$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.12	0.4	>	$I_C = 1.5A, I_B = 75mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	0.9	1.2	>	$I_C = 1.5A$, $I_B = 75mA$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f⊤	_	300		MHz	$V_{CE} = 10V, I_{C} = 50mA,$
Carrent Carr Banawati i Todact	''		000		1711 12	f = 100MHz
Output Capacitance	C _{obo}	_	16		pF	$V_{CB} = 10V$, $I_{E} = 0$, $f = 1MHz$
SWITCHING CHARACTERISTICS						
Turn On Time	t _{on}	_	70	_	ns	V - 13V V - 5V
Storage Time	t _{stg}		170		ns	$V_{CE} = 12V, V_{BE} = 5V,$
Fall Time	t _f		25		ns	$I_{B1} = I_{B2} = 25$ mA, $I_{C} = 500$ mA

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.







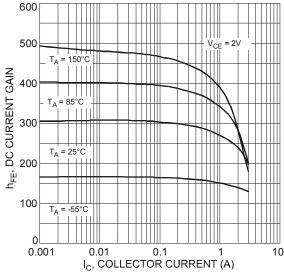


Fig. 3 Typical DC Current Gain vs. Collector Current

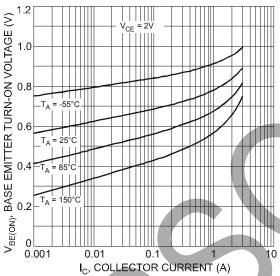


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

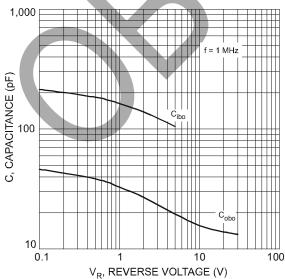


Fig. 7 Typical Junction Capacitance Characteristics

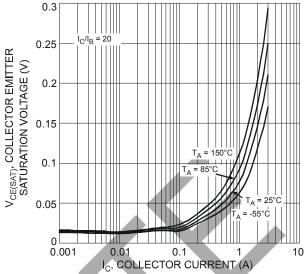


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

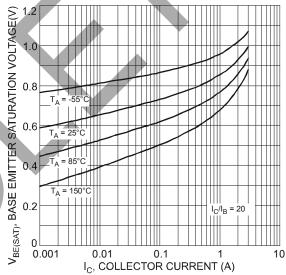


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

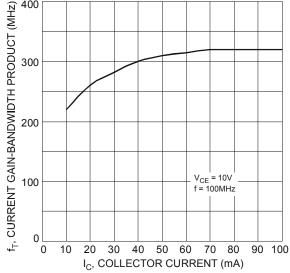


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

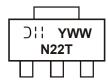


Ordering Information (Note 5)

Part Number	Case	Packaging	
2DD1621T-13	SOT89-3L	2500/Tape & Reel	

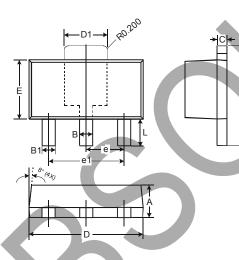
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



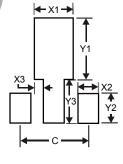
N22T = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex; 7 = 2007) WW = Week code (01 – 53)

Package Outline Dimensions



SOT89-3L				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
O	0.35	0.43		
D	4.40	4.60		
D1	1.52	1.83		
Е	2.29	2.60		
е	1.50 Typ			
e1	3.00 Typ			
Η	3.94	4.25		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
Х3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
С	3.0



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